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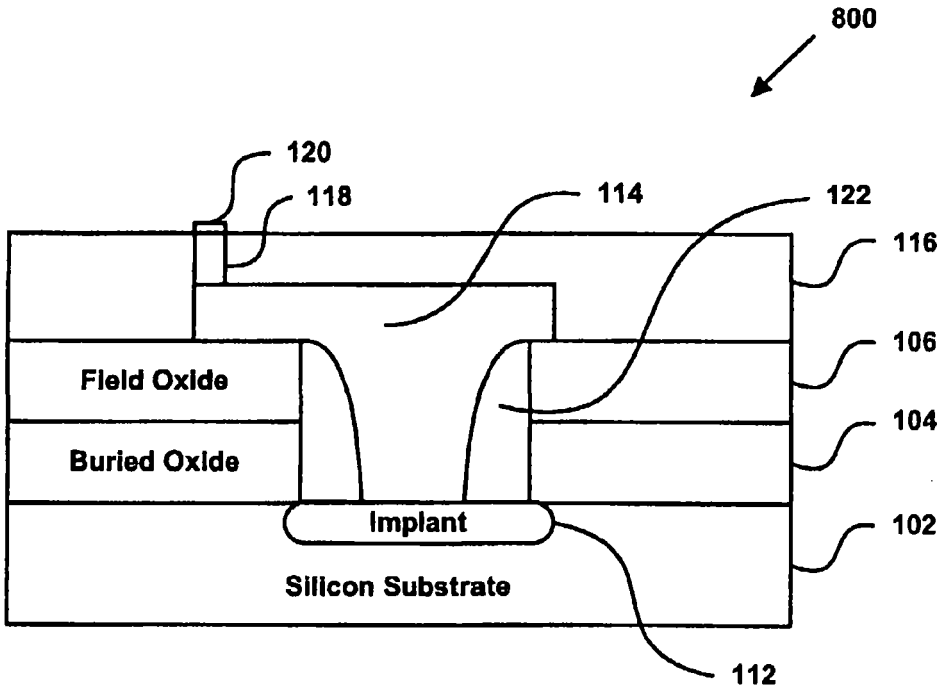
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(54) Title: FORMATION OF A FRONTSIDE CONTACT ON SILICON-ON-INSULATOR SUBSTRATE



(57) Abstract: A method of forming a frontside contact to a Silicon-On-Insulator (SOI) wafer is described. A connection polysilicon (114) connects a silicon substrate layer (102) to a contact plug (118). This connection provides a means to ground or bias the bottom substrate of the SOI wafer. Spacers (122) may be added to provide additional doping.

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